

**1. Material** Substrate GaAs (N Type)  
Epitaxial Layer AlGaInP (P/N Type)

**2. Electrode** N(Cathode) Side Gold Alloy  
P(Anode) Side Gold Alloy

**3. Electro-Optical Characteristics**

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_F$		2.1	2.4	V	IF=20mA
Reverse Current	$I_R$			100	uA	VR=5V
Brightness	$I_v$	B	90	120	mcd	IF=20mA
		C	110	140		
		D	130	160		
		E	140	180		
		F	140	200		
Wavelength	$\lambda_d$		620		nm	IF=20mA
	$\Delta\lambda$		20		nm	IF=20mA

※ Note : Luminous Intensity is measured on bare chips.

**4. Mechanical Data** (a) Emission Area ----- 11mil x 11mil  
 (b) Bottom Area ----- 12mil x 12mil  
 (c) Bonding Pad ----- 100um  
 (d) Chip Thickness ----- 7mil

